

FEATURES

- High Thermal Cycling Capability
- Non Punch Through Silicon
- Isolated MMC Base with AlN Substrates

APPLICATIONS

- High Reliability Inverters
- Motor Controllers
- Traction Drives
- Resonant Converters

The Powerline range of high power modules includes dual and single switch configurations covering voltages from 1200V to 3300V and currents up to 4800A.

The GP1200ESM33 is a single switch 3300V, n channel enhancement mode, insulated gate bipolar transistor (IGBT) module. The IGBT has a wide reverse bias safe operating area (RBSOA) ensuring reliability in demanding applications. This device is optimised for traction drives and other applications requiring high thermal cycling capability or very high reliability.

The module incorporates an electrically isolated base plate and low inductance construction enabling circuit designers to optimise circuit layouts and utilise grounded heat sinks for safety.

ORDERING INFORMATION

Order As:

GP1200ESM33

Note: When ordering, please use the whole part number.

KEY PARAMETERS

V_{CES}		3300V
$V_{CE(sat)}$	(typ)	3.4V
I_C	(max)	1200A
$I_{C(PK)}$	(max)	2400A

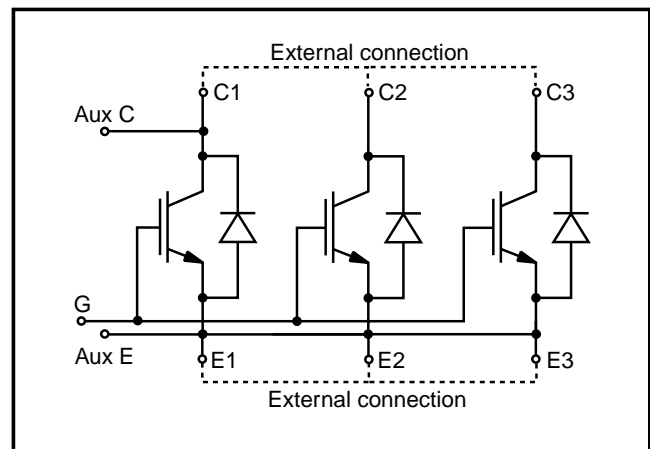
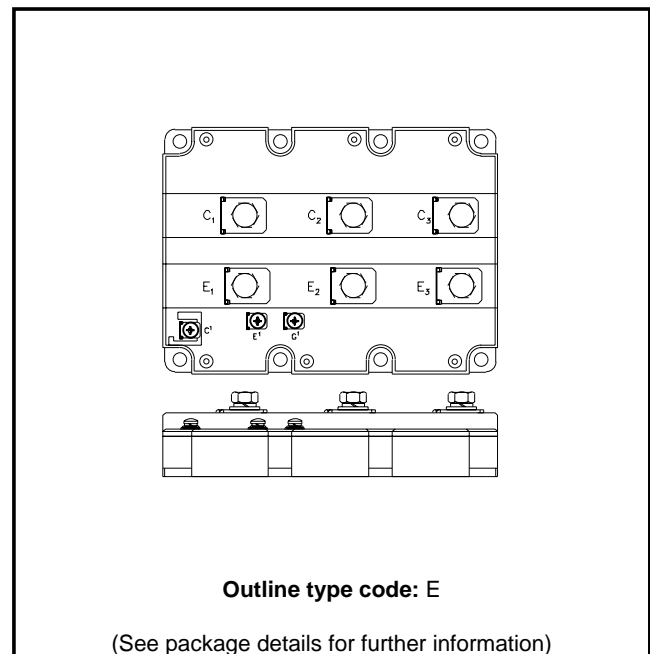


Fig. 1 Single switch circuit diagram



Outline type code: E

(See package details for further information)

Fig. 2 Electrical connections - (not to scale)

ABSOLUTE MAXIMUM RATINGS

Stresses above those listed under 'Absolute Maximum Ratings' may cause permanent damage to the device. In extreme conditions, as with all semiconductors, this may include potentially hazardous rupture of the package. Appropriate safety precautions should always be followed. Exposure to Absolute Maximum Ratings may affect device reliability.

$T_{case} = 25^{\circ}\text{C}$ unless stated otherwise

Symbol	Parameter	Test Conditions	Max.	Units
V_{CES}	Collector-emitter voltage	$V_{GE} = 0V$	3300	V
V_{GES}	Gate-emitter voltage	-	± 20	V
I_C	Continuous collector current	$T_{case} = 80^{\circ}\text{C}$	1200	A
$I_{C(PK)}$	Peak collector current	1ms, $T_{case} = 120^{\circ}\text{C}$	2400	A
P_{max}	Max. transistor power dissipation	$T_{case} = 25^{\circ}\text{C}$, $T_j = 150^{\circ}\text{C}$	14.7	kW
V_{isol}	Isolation voltage	Commoned terminals to base plate. AC RMS, 1 min, 50Hz	6000	V

THERMAL AND MECHANICAL RATINGS

Symbol	Parameter	Test Conditions	Min.	Max.	Units
$R_{th(j-c)}$	Thermal resistance - transistor	Continuous dissipation - junction to case	-	8.5	$^{\circ}\text{C}/\text{kW}$
$R_{th(f-c)}$	Thermal resistance - diode	Continuous dissipation - junction to case	-	16.3	$^{\circ}\text{C}/\text{kW}$
$R_{th(c-h)}$	Thermal resistance - case to heatsink (per module)	Mounting torque 5Nm (with mounting grease)	-	4	$^{\circ}\text{C}/\text{kW}$
T_j	Junction temperature	Transistor	-	125	$^{\circ}\text{C}$
		Diode	-	125	$^{\circ}\text{C}$
T_{stg}	Storage temperature range	-	-40	125	$^{\circ}\text{C}$
-	Screw torque	Mounting - M6	-	5	Nm
		Electrical connections - M4	-	2	Nm
		Electrical connections - M8	-	10	Nm

ELECTRICAL CHARACTERISTICS
 $T_{case} = 25^{\circ}\text{C}$ unless stated otherwise.

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
I_{CES}	Collector cut-off current	$V_{GE} = 0\text{V}, V_{CE} = V_{CES}$	-	-	3	mA
		$V_{GE} = 0\text{V}, V_{CE} = V_{CES}, T_{case} = 125^{\circ}\text{C}$	-	-	100	mA
I_{GES}	Gate leakage current	$V_{GE} = \pm 20\text{V}, V_{CE} = 0\text{V}$	-	-	12	μA
$V_{GE(TH)}$	Gate threshold voltage	$I_C = 120\text{mA}, V_{GE} = V_{CE}$	4.5	5.5	6.5	V
$V_{CE(sat)}$	Collector-emitter saturation voltage	$V_{GE} = 15\text{V}, I_C = 1200\text{A}$	-	3.4	4.3	V
		$V_{GE} = 15\text{V}, I_C = 1200\text{A}, T_{case} = 125^{\circ}\text{C}$	-	4.3	5	V
I_F	Diode forward current	DC	-	-	1200	A
I_{FM}	Diode maximum forward current	$t_p = 1\text{ms}$	-	-	2400	A
V_F	Diode forward voltage	$I_F = 1200\text{A}$	-	2.3	2.9	V
		$I_F = 1200\text{A}, T_{case} = 125^{\circ}\text{C}$	-	2.4	3	V
C_{ies}	Input capacitance	$V_{CE} = 25\text{V}, V_{GE} = 0\text{V}, f = 1\text{MHz}$	-	300	-	nF
L_M	Module inductance	-	-	10	-	nH

ELECTRICAL CHARACTERISTICS

 $T_{\text{case}} = 25^{\circ}\text{C}$ unless stated otherwise

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
$t_{\text{d(off)}}$	Turn-off delay time	$I_{\text{C}} = 1200\text{A}$ $V_{\text{GE}} = \pm 15\text{V}$ $V_{\text{CE}} = 1800\text{V}$ $R_{\text{G(ON)}} = 1.8\Omega, R_{\text{G(OFF)}} = 3.3\Omega$ $C_{\text{GE}} = 660\text{nF},$ $L \sim 90\text{nH}$	-	3.2	-	μs
t_{f}	Fall time		-	0.9	-	μs
E_{OFF}	Turn-off energy loss		-	1.6	-	J
$t_{\text{d(on)}}$	Turn-on delay time		-	1.1	-	μs
t_{r}	Rise time		-	0.4	-	μs
E_{ON}	Turn-on energy loss		-	1.6	-	J
Q_{rr}	Diode reverse recovery charge	$I_{\text{F}} = 1200\text{A}, V_{\text{R}} = 1800\text{V},$ $di_{\text{F}}/dt = 5500\text{A}/\mu\text{s}$	-	600	-	μC
I_{rr}	Diode reverse current		-	1200	-	A
E_{REC}	Diode reverse recovery energy		-	0.7	-	J

 $T_{\text{case}} = 125^{\circ}\text{C}$ unless stated otherwise

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
$t_{\text{d(off)}}$	Turn-off delay time	$I_{\text{C}} = 1200\text{A}$ $V_{\text{GE}} = \pm 15\text{V}$ $V_{\text{CE}} = 1800\text{V}$ $R_{\text{G(ON)}} = 1.8\Omega, R_{\text{G(OFF)}} = 3.3\Omega$ $C_{\text{GE}} = 660\text{nF},$ $L \sim 90\text{nH}$	-	3.4	-	μs
t_{f}	Fall time		-	1.5	-	μs
E_{OFF}	Turn-off energy loss		-	2.4	-	J
$t_{\text{d(on)}}$	Turn-on delay time		-	1.1	-	μs
t_{r}	Rise time		-	0.5	-	μs
E_{ON}	Turn-on energy loss		-	2.3	-	J
Q_{rr}	Diode reverse recovery charge	$I_{\text{F}} = 1200\text{A}, V_{\text{R}} = 1800\text{V},$ $di_{\text{F}}/dt = 4500\text{A}/\mu\text{s}$	-	1000	-	μC
I_{rr}	Diode reverse current		-	1300	-	A
E_{REC}	Diode reverse recovery energy		-	1.1	-	J

TYPICAL CHARACTERISTICS

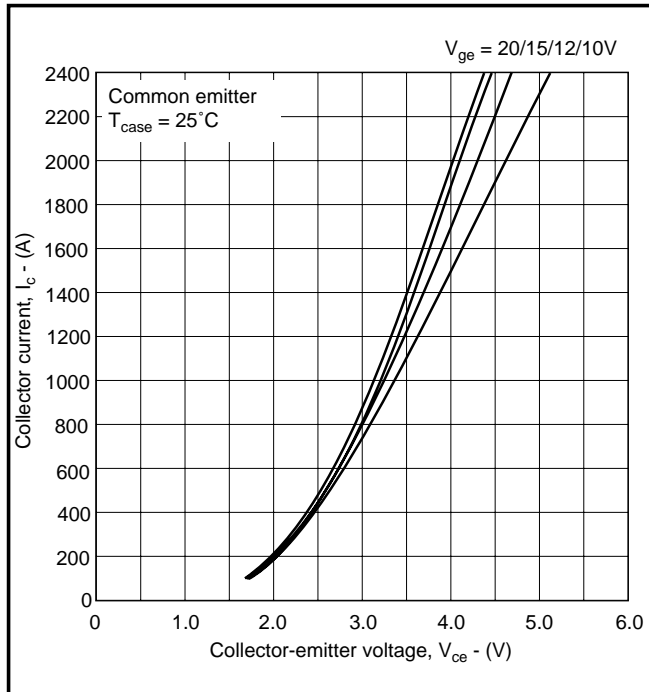


Fig.3 Typical output characteristics

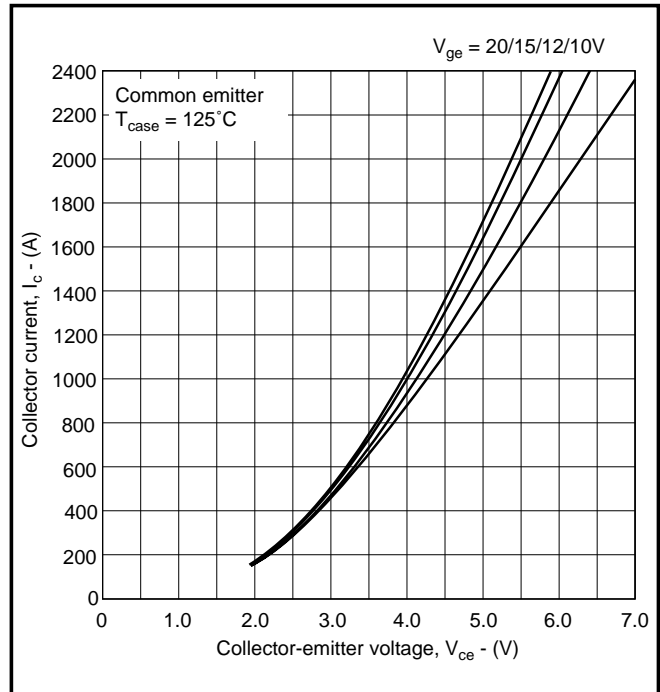


Fig.4 Typical output characteristics

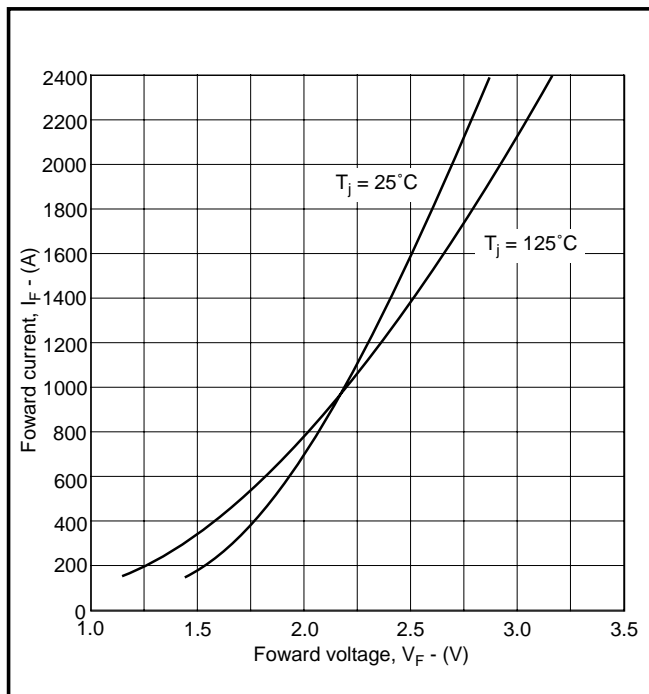


Fig.5 Diode typical forward characteristics

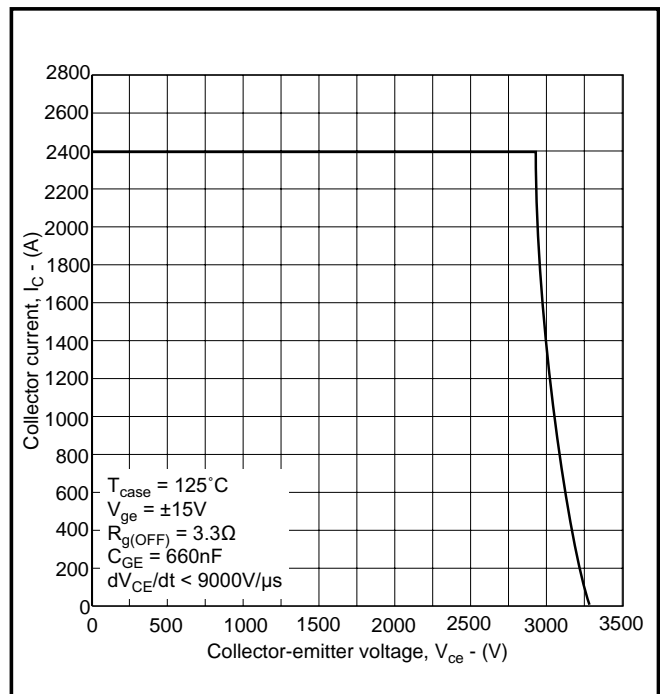


Fig.6 Reverse bias safe operating area

Caution: This device is sensitive to electrostatic discharge. Users should follow ESD handling procedures.

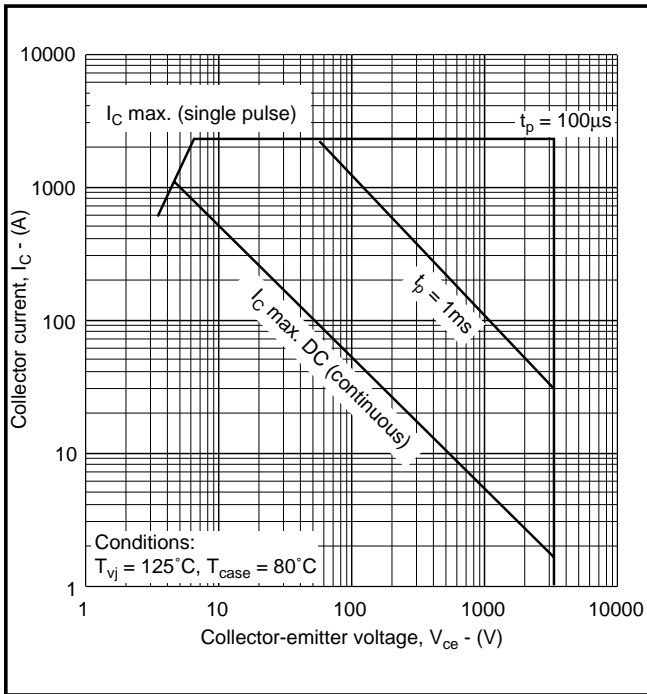


Fig.7 Forward bias safe operating area

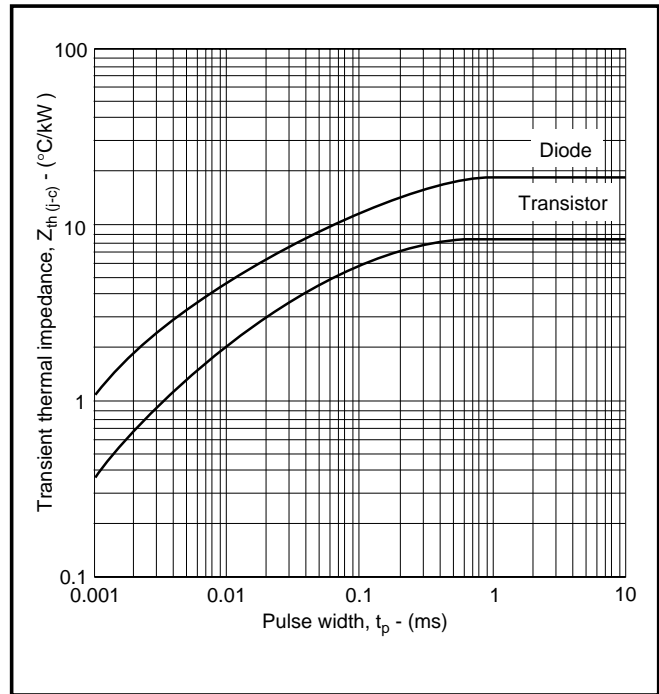


Fig.8 Transient thermal impedance

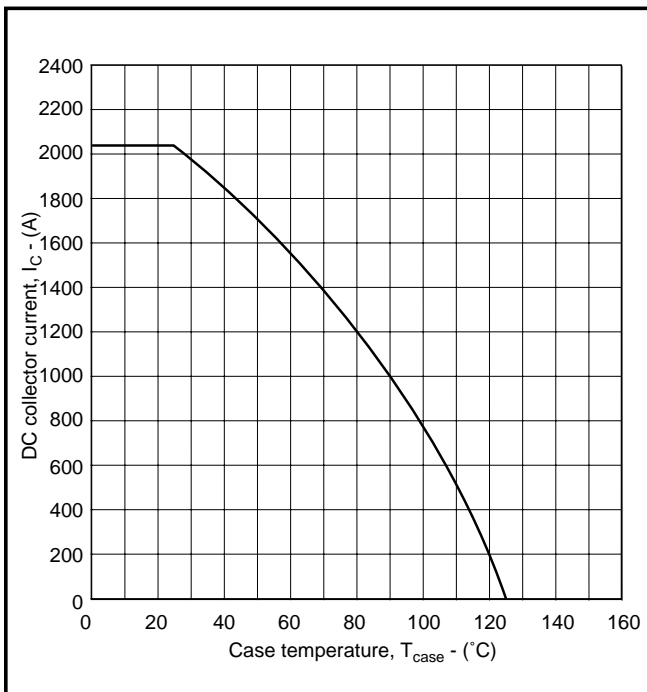


Fig.9 DC current rating vs case temperature

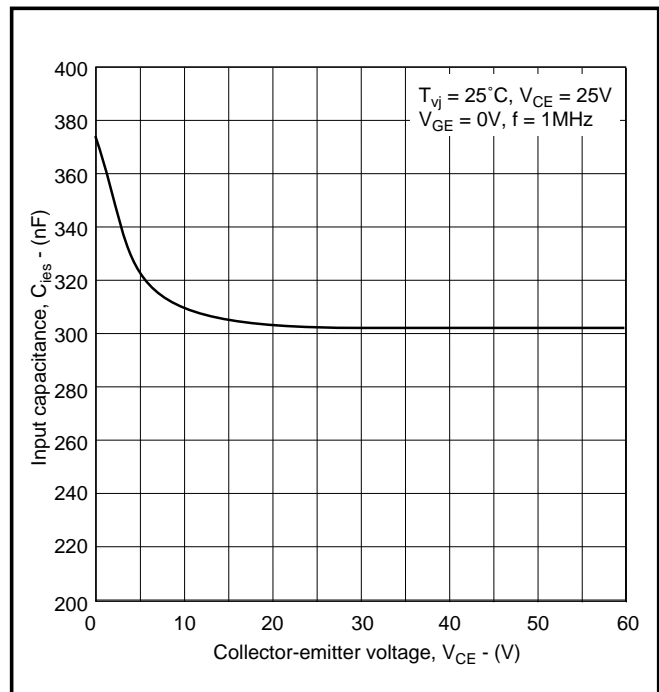
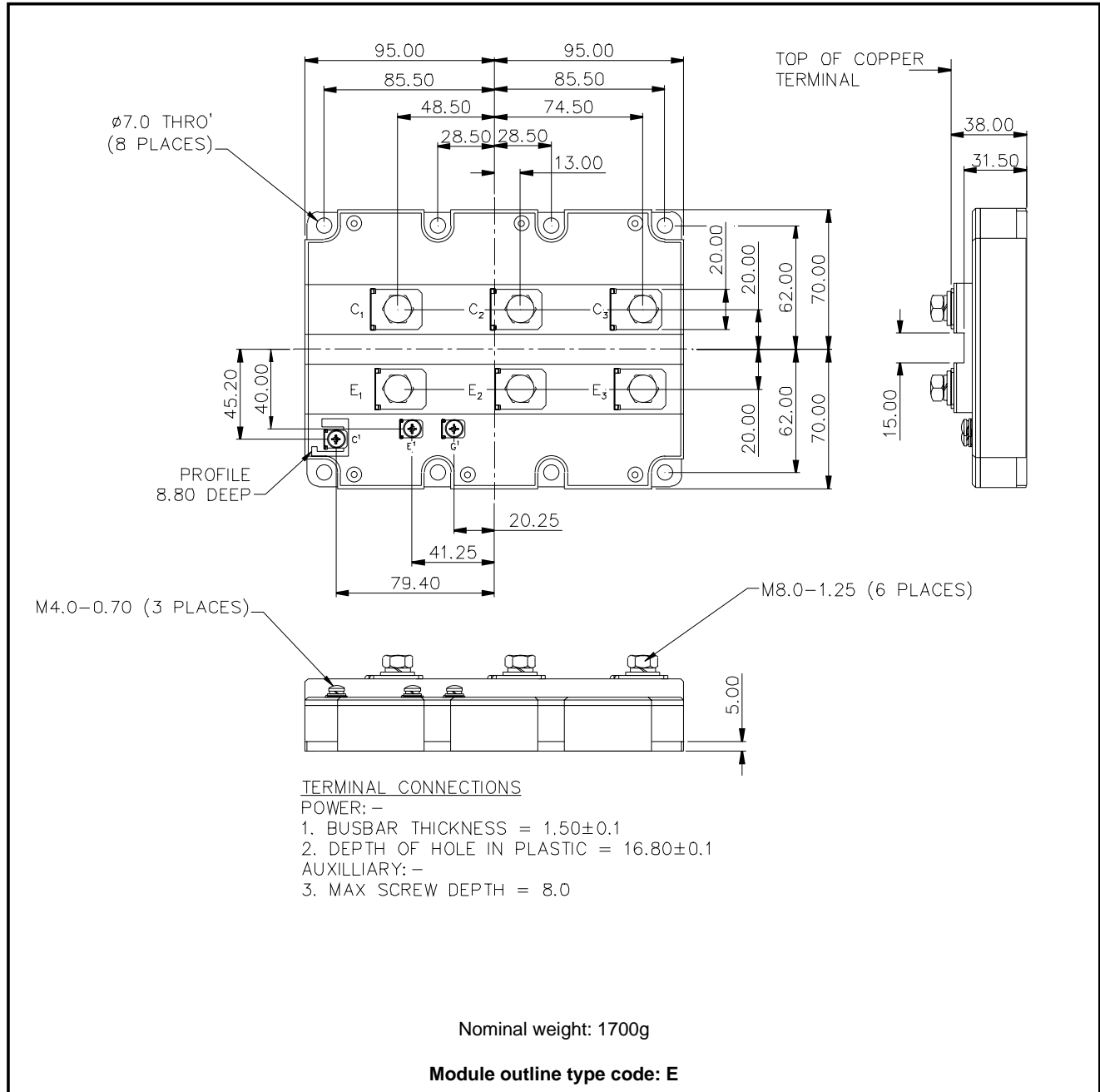


Fig.10 Typical input capacitance

PACKAGE DETAILS

For further package information, please visit our website or contact your nearest Customer Service Centre. All dimensions in mm, unless stated otherwise. **DO NOT SCALE.**



Caution: This device is sensitive to electrostatic discharge. Users should follow ESD handling procedures.

ASSOCIATED PUBLICATIONS

Title	Application Note
	Number
Electrostatic handling precautions	AN4502
An introduction to IGBTs	AN4503
IGBT ratings and characteristics	AN4504
Heatsink requirements for IGBT modules	AN4505
Calculating the junction temperature of power semiconductors	AN4506
Gate drive considerations to maximise IGBT efficiency	AN4507
Parallel operation of IGBTs – punch through vs non-punch through characteristics	AN4508
Guidance notes for formulating technical enquiries	AN4869
Principle of rating parallel connected IGBT modules	AN5000
Short circuit withstand capability in IGBTs	AN5167
Driving high power IGBTs with Concept gate drivers	AN5190

POWER ASSEMBLY CAPABILITY

The Power Assembly group provides support for those customers requiring more than the basic semiconductor switch. Using CAD design tools the group has developed a flexible range of heatsink / clamping systems in line with advances in device types and the voltage and current capability of Dynex semiconductors.

An extensive range of air and liquid cooled assemblies is available covering the range of circuit designs in general use today.

HEATSINKS

The Power Assembly group has a proprietary range of extruded aluminium heatsinks. These were designed to optimise the performance of Dynex semiconductors. Data with respect to air natural, forced air and liquid cooling (with flow rates) is available on request.

For further information on device clamps, heatsinks and assemblies, please contact your nearest sales representative or customer service office.



<http://www.dynexsemi.com>

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Preliminary Information: The product is in design and development. The datasheet represents the product as it is understood but details may change.

Advance Information: The product design is complete and final characterisation for volume production is well in hand.

No Annotation: The product parameters are fixed and the product is available to datasheet specification.

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